Nov. 2005

THE SPECIFICATION OF AlGaAs IR LED CHIP "NR4JN83 "

1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is N-side up. The peak wavelength is 780 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25℃)

CONDITION			MIN.	TYP.	MAX.	UNIT
Forward Voltage	(V_F)	IF=20mA		1.7		V
Reverse Voltage	(V_R)	IR=10μA	5.0			V
Radiated Power[1)]	(Po)	IF=20mA	3.0			mW
Peak Wavelength	(λ_P)	IF=20mA		780		nm
Spectral Radiation Bandwidth	(Δλ)	IF=20mA		30		nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Storage Temperature
while on mylar membrane : 0 to 40 ℃
after removal from mylar membrane : -30 to 100 ℃

4. PHYSICAL CHRACTERISTICS AND STRUCTURE

1) Material : AlGaAs
2) Structure : Double Hetero Structure
3) Junction Size : 0.320mmX0.320mm
4) Thickness : 0.150mm
5) Bond Pad Size : 0.140mm diameter
6) Anode Metallization : Gold Alloy
7) Cathode Metallization: Gold Alloy

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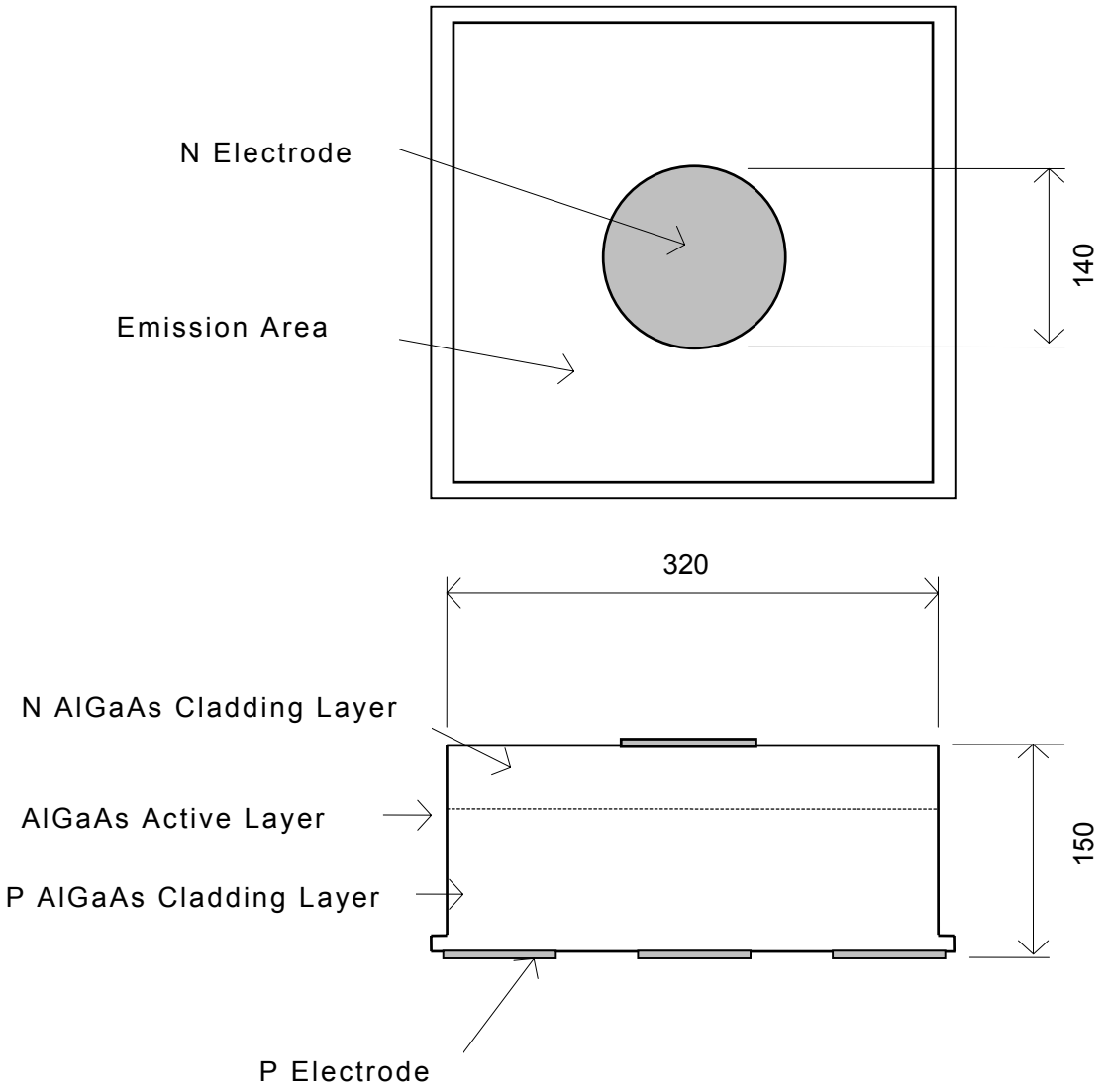
Physical Dimensions

Model NR4JN83

UNIT: um



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.